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Method of oxidizing a substrate in the presence of nitride and oxynitride films

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A system and method of forming an oxide in the presence of a nitrogen-containing material. A substrate having a nitrogen-containing material on a surface is placed in a reaction chamber. An oxygen-containing gas, or an oxygen-containing gas and a hydrogen-containing gas are provided to the chamber and reacted in the chamber. The reactive gases are used to oxidize the surface of the substrate and displace the nitrogen-containing material from the interface.

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